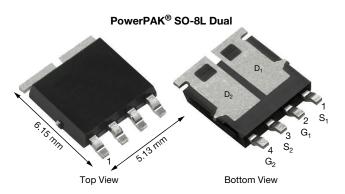


Vishay Siliconix

# Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	- 30
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -10 \text{ V}$	0.017
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -4.5 \text{ V}$	0.036
I <sub>D</sub> (A)	- 30
Configuration	Dual

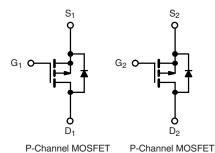
#### **FEATURES**

- TrenchFET® Power MOSFET
- AEC-Q101 qualified <sup>d</sup>
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJ951EP (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unles	ss otherwise noted	)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	- 30	
Gate-source voltage		$V_{GS}$	± 20	V
Continuous drain current	$T_C = 25  ^{\circ}C^{a}$	1	- 30	
Continuous drain current	T <sub>C</sub> = 125 °C	l <sub>D</sub>	- 28	
Continuous source current (diode conductio	n) <sup>a</sup>	I <sub>S</sub>	- 30	Α
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	- 120	
ngle pulse avalanche current		I <sub>AS</sub>	- 27	
Single pulse avalanche energy	L=0.11III	E <sub>AS</sub>	36.5	mJ
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	В	56	W
Maximum power dissipation ~	issipation b $T_C = 125 ^{\circ}\text{C}$ $P_D$ $W$	VV		
Operating junction and storage temperature	range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C
Soldering recommendations (peak temperature) e, f			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	R <sub>thJA</sub>	85	°C/W
Junction-to-case (drain)		$R_{thJC}$	2.7	C/VV

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing
- e. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	•						,
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = - 250 μA		- 30	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1.5	- 2.0	- 2.5	]
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = - 30 V	-	-	- 1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 125 °C	-	-	- 50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 175 °C	-	-	- 150	
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	V <sub>DS</sub> = - 5 V	- 30	-	-	Α
B :		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 7.5 A	-	0.014	0.017	Ω
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 7.5A, T <sub>J</sub> = 125 °C	-	-	0.034	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 7.5 A, T <sub>J</sub> = 175 °C	-	-	0.039	
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 5 A	-	0.030	0.036	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 7.5 A		-	18	-	S
Dynamic <sup>b</sup>	·						
Input capacitance	C <sub>iss</sub>			-	1345	1680	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 10 V, f = 1 MHz	-	330	415	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	245	305	
Total gate charge <sup>c</sup>	Qg			-	33	50	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 9 A	-	5.5	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	9.4		
Gate resistance	R <sub>g</sub>	f = 1 MHz		3	6.31	10.5	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	12	18	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 1.66 $\Omega$ $I_D$ $\cong$ - 9 A, $V_{GEN}$ = - 10 V, $R_g$ = 6 $\Omega$		-	12	18	ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	39	59	
Fall time <sup>c</sup>	t <sub>f</sub>	7		-	28	42	1
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>	•					
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	- 120	Α
Forward voltage	$V_{SD}$	Ic =	- 4.5 A, V <sub>GS</sub> = 0	_	- 0.8	- 1.2	V

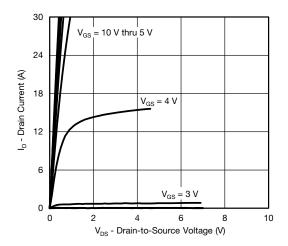
## Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

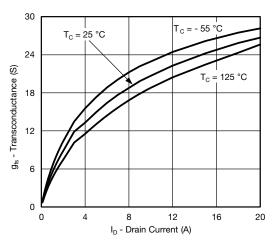
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



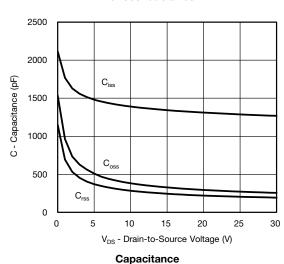
# TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



## **Output Characteristics**



## Transconductance

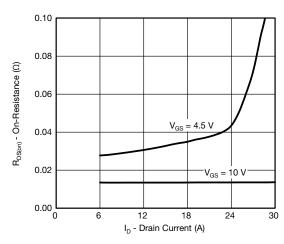


30
24

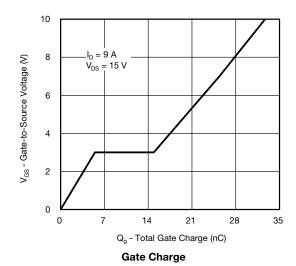
(x)

18  $T_{c} = 125 \, ^{\circ}\text{C}$   $T_{c} = 125 \, ^{\circ}\text{C}$   $T_{c} = -55 \, ^{\circ}\text{C}$ 

### **Transfer Characteristics**

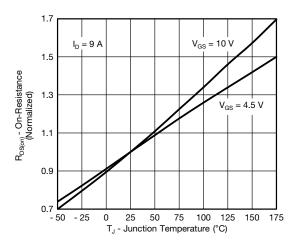


## **On-Resistance vs. Drain Current**

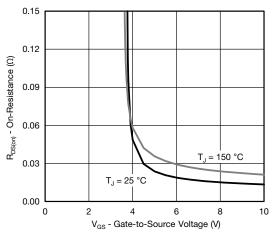


TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

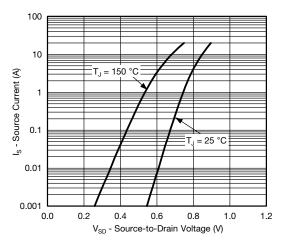




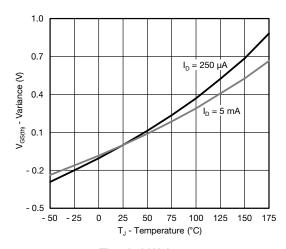
#### On-Resistance vs. Junction Temperature



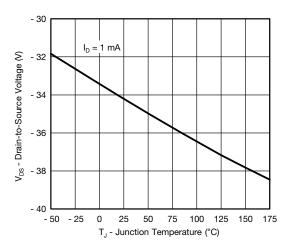
On-Resistance vs. Gate-to-Source Voltage



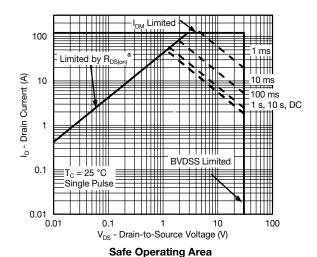
**Source Drain Diode Forward Voltage** 



## **Threshold Voltage**



**BVDSS** vs. Junction Temperature

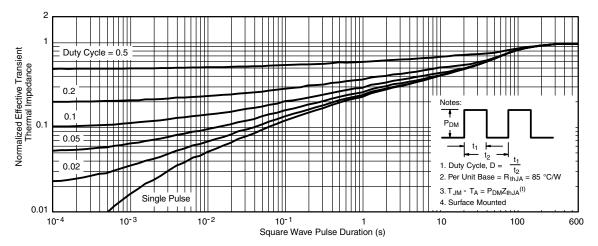


#### Note

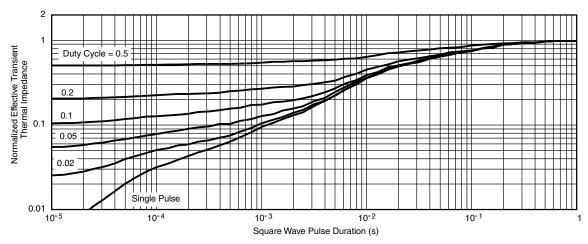
a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



# **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?63658">www.vishay.com/ppg?63658</a>.



# PowerPAK® SO-8L Case Outline 2



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DIM		MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN. NOM.		MAX.		
Α	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094			0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC		0.050 BSC				
Е	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
E3	6.05	6.22	6.40	0.238	0.245	0.252		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
K		0.51			0.020			
W		0.23			0.009			
W1		0.41			0.016			
W2	2.82			0.111				
W3		2.96			2.96 0.117			
θ	0°	-	10°	0°	-	10°		

DWG: 6044

#### Note

• Millimeters will govern



## RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)



# **Legal Disclaimer Notice**

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